

Insulated Gate Bipolar Transistor

Standard & Fast Processes

Part Number	BV _{CES} Collector to Emitter Breakdown Voltage (V)	V _{GE(th)} Gate to Emitter Threshold Voltage		V _{CE(on)} Collector to Emitter Saturation Voltage (1)		I _C @ Collector Current @ T _C = 25°C (A)	E _{ts} typ Total Switching Loss @ T _J = 150°C V _{CC} = 400V (mJ) (A)		P _D Max. Power Dissip. (W)	Case Outline Number (2)	Notes	Case Style
		Min (V)	Max (V)	Typ (V)	Max (V)							
IRGBC20	600	2.5	5.0	2.7	3.4	13	0.9	6.5	60	IG1	(2)	TO-220AB
IRGBC26				1.8	2.4	19	6.2	10	60			
IRGBC30				2.6	3.2	23	1.7	12	100			
IRGBC36				1.7	2.2	34	11.9	18	100			
IRGBC40				2.4	3.0	40	2.7	20	160			
IRGBC46				1.6	2.0	50	20.8	31	160			
IRGPC40				2.4	3.0	40	2.7	20	160	IG2	(2)	TO-247AC (TO-3P)
IRGPC46				1.6	2.0	60	21.4	31	160			
IRGPC50				2.2	2.7	55	4.1	27	200			
IRGPC56				1.4	1.8	70	28.6	41	200			



- (1) PULSE TEST, 80 μ s DUTY FACTOR <0.1%.
- (2) FOR CASE OUTLINE DRAWING SEE REAR OF SECTION.